

SANYO**SB40W03T**

Schottky Barrier Diode (Twin Type · Cathode Common)

30V, 4A Rectifier**Applications**

- High frequency rectification (switching regulators, converters, choppers).

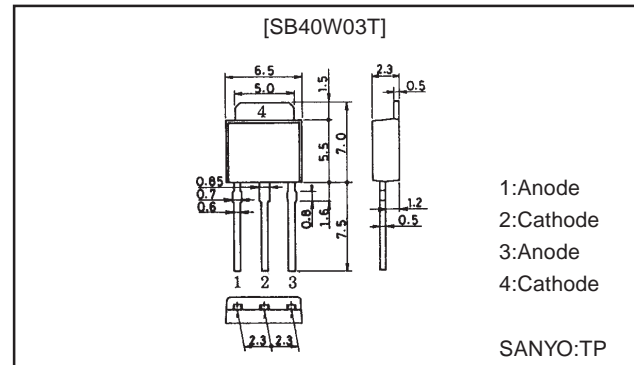
Features

- Low forward voltage (V_F max=0.55V).
- Fast reverse recovery time (t_{rr} max=30ns).
- Low switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.

Package Dimensions

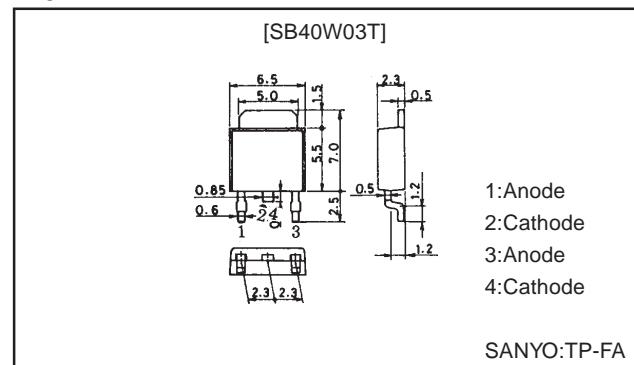
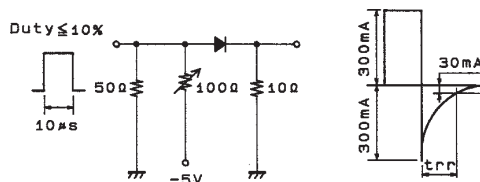
unit:mm

1254A



unit:mm

1257A

 **t_{rr} Test Circuit****Specifications****Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$ (Value per element)**

| Parameter | Symbol | Conditions | Ratings | Unit |
|--|-----------|---|-------------|------------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 30 | V |
| Nonrepetitive Peak Reverse Surge Voltage | V_{RSM} | | 35 | V |
| Average Output Current | I_O | 50Hz, resistive load, $T_c=111^\circ\text{C}$ | 4 | A |
| | I_O | 50Hz, resistive load, $T_c=92^\circ\text{C}$, Total rating | 8 | A |
| Surge Forward Current | I_{FSM} | 50Hz sine wave, 1 cycle | 40 | A |
| Junction Temperature | T_J | | -55 to +125 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | | -55 to +125 | $^\circ\text{C}$ |

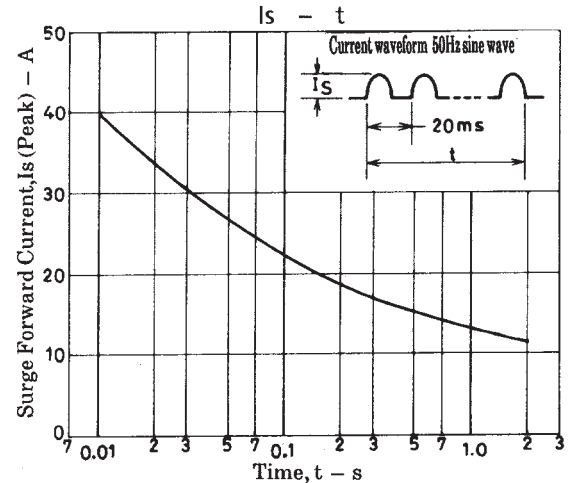
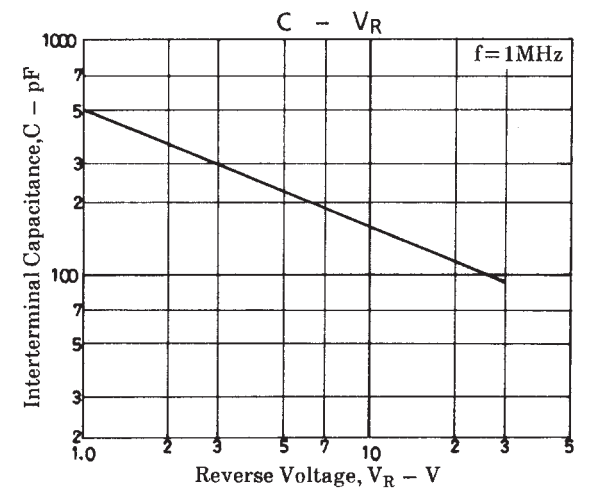
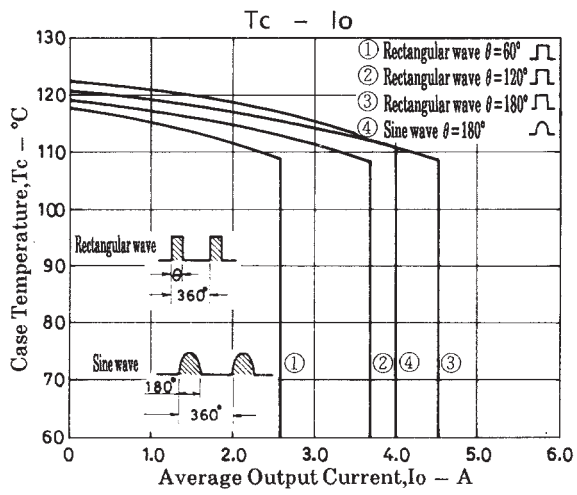
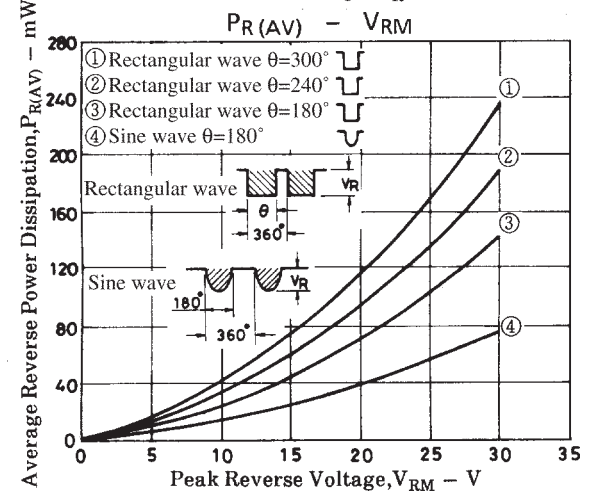
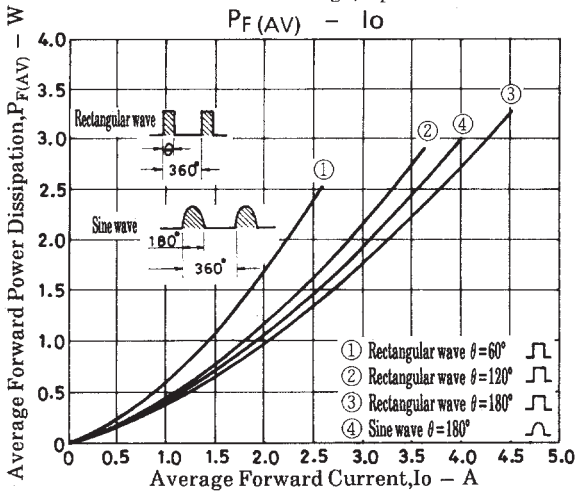
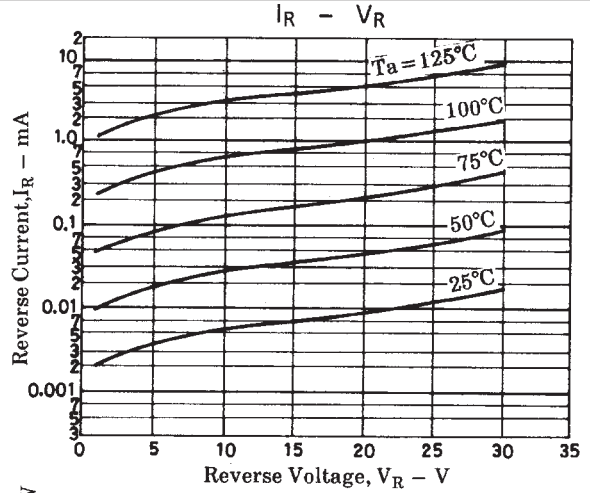
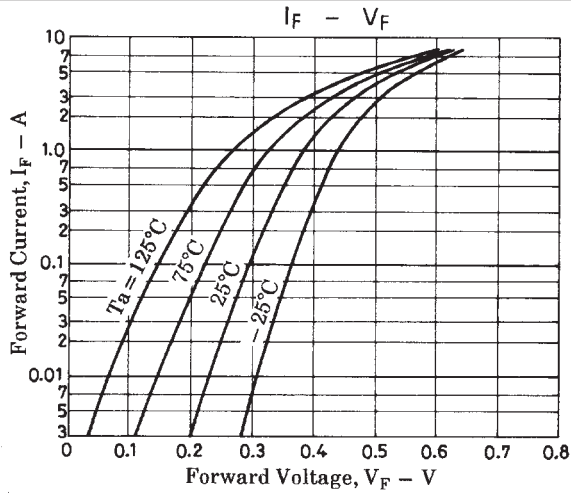
Electrical Characteristics at $T_a = 25^\circ\text{C}$ (Value per element)

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---------------------------------------|---------------|--|---------|-----|------|--------------------|
| | | | min | typ | max | |
| Reverse Voltage | V_R | $I_R=1\text{mA}$ | 30 | | | V |
| Forward Voltage | $V_F(1)$ | $I_F=4\text{A}$ | | | 0.55 | V |
| | $V_F(2)$ | $I_F=1\text{A}$ | | | 0.45 | V |
| Reverse Current | I_R | $V_R=15\text{V}$ | | | 200 | μA |
| Interterminal Capacitance | C | $V_R=10\text{V}$, $f=1\text{MHz}$ | | 160 | | pF |
| Reverse Recovery Time | t_{rr} | $I_F=I_R=300\text{mA}$, See specified Test Circuit. | | | 30 | ns |
| Thermal Resistance (Junction-Ambient) | $R_{th(j-a)}$ | | | 90 | | $^\circ\text{C/W}$ |
| Thermal Resistance (Junction-Case) | $R_{th(j-c)}$ | | | 5 | | $^\circ\text{C/W}$ |

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